

Appl. No. 09/905,053
Amdt. dated September 3, 2003
Reply to Office Action of June 4, 2003

PATENT

AMENDMENTS

In the Specification:

Please amend paragraph [0017] to read as follows:

[0017] Referring to Figure 4B, in a first stage, a first layer 108 is deposited in the recesses 27 and over the substrate 100. In this stage, a deposition gas composition that provides different deposition rates depending upon the underlying material upon which the deposition occurs, is used. In one version, the deposition gas comprises an oxygen-containing compound, such as one or more of O₃ or TEOS. A suitable deposition gas composition comprises first and second components, such as O₃ and TEOS, in a volumetric flow ratio that provides different deposition rates on silicon or silicon nitride material. The deposition gas, when energized to form a plasma, deposits a first layer 108 of silicon oxide on the liner 106. The first layer 106 108 is formed using the bottom-up growth mechanism for smoothening the profile of the recesses 107 by filling any reentrant cavities. However, the recesses 107 are not entirely filled in this step and other sequential deposition steps may be used to fill the recesses 107.